



# Standard Rectifier Module

$V_{RRM} = 2 \times 800 \text{ V}$

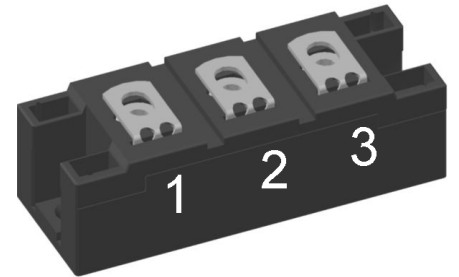
$I_{FAV} = 190 \text{ A}$

$V_F = 0.96 \text{ V}$

Phase leg

Part number

**MDD172-08N1**



Backside: isolated



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

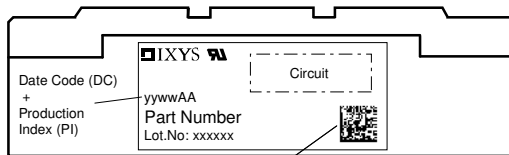
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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			900	V	
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			800	V	
$I_R$	reverse current	$V_R = 800 V$	$T_{VJ} = 25^{\circ}C$		1	mA	
		$V_R = 800 V$	$T_{VJ} = 150^{\circ}C$		20	mA	
$V_F$	forward voltage drop	$I_F = 150 A$	$T_{VJ} = 25^{\circ}C$		1.07	V	
		$I_F = 300 A$			1.22	V	
		$I_F = 150 A$	$T_{VJ} = 125^{\circ}C$		0.96	V	
		$I_F = 300 A$			1.16	V	
$I_{FAV}$	average forward current	$T_C = 100^{\circ}C$	$T_{VJ} = 150^{\circ}C$		190	A	
$I_{F(RMS)}$	RMS forward current	180° sine			300	A	
$V_{F0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.80	V	
$r_F$	slope resistance				0.8	mΩ	
$R_{thJC}$	thermal resistance junction to case				0.21	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.08		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		600	W	
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		6.60	kA	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		7.13	kA	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		5.61	kA	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		6.06	kA	
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		217.8	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		211.5	kA <sup>2</sup> s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		157.4	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		152.8	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		238	pF	



Package Y4				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			300	A	
$T_{VJ}$	virtual junction temperature		-40		150	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		125	°C	
<b>Weight</b>					150	g	
$M_D$	mounting torque		2.25		2.75	Nm	
$M_T$	terminal torque		4.5		5.5	Nm	
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	14.0	10.0		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
$V_{ISOL}$	isolation voltage	t = 1 second			3600	V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3000	V	



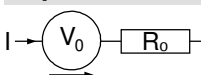
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD172-08N1	MDD172-08N1	Box	6	429694

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$



**Rectifier**

$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	0.4	mΩ



**Outlines Y4**



Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	



**Rectifier**

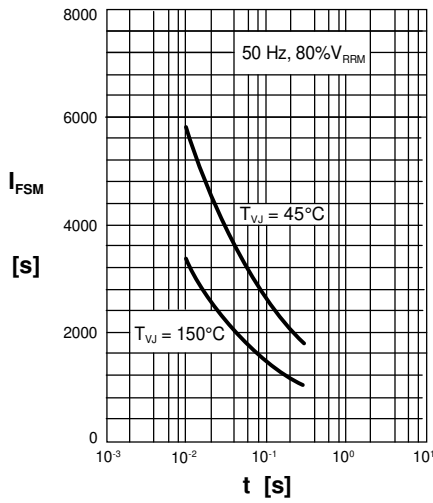


Fig. 1 Surge overload current  
 $I_{FSM}$ : Crest value, t: duration

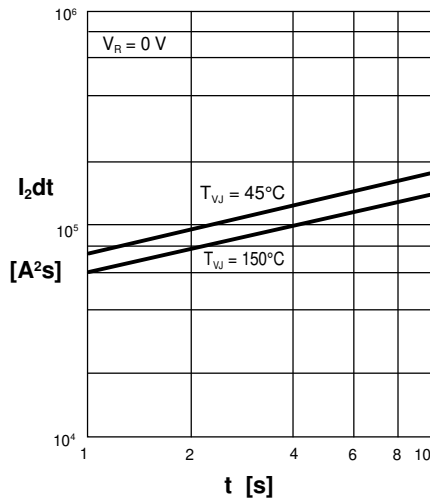


Fig. 2  $I_2dt$  versus time (1-10 ms)

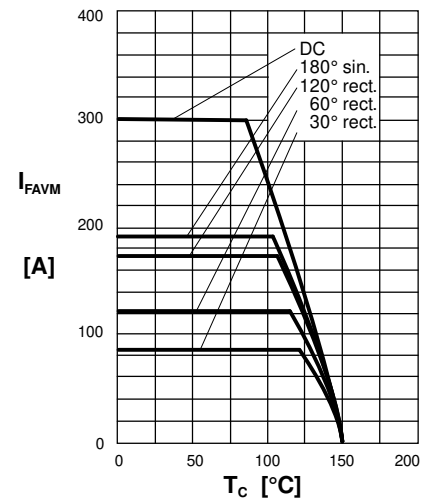


Fig. 2a Maximum forward current at case temperature

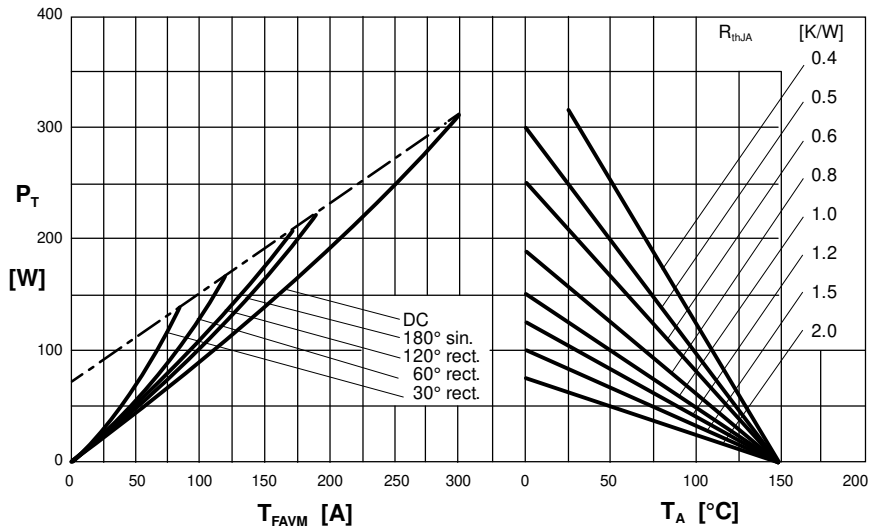


Fig. 3 Power dissipation vs. forward current and ambient temperature (per diode)

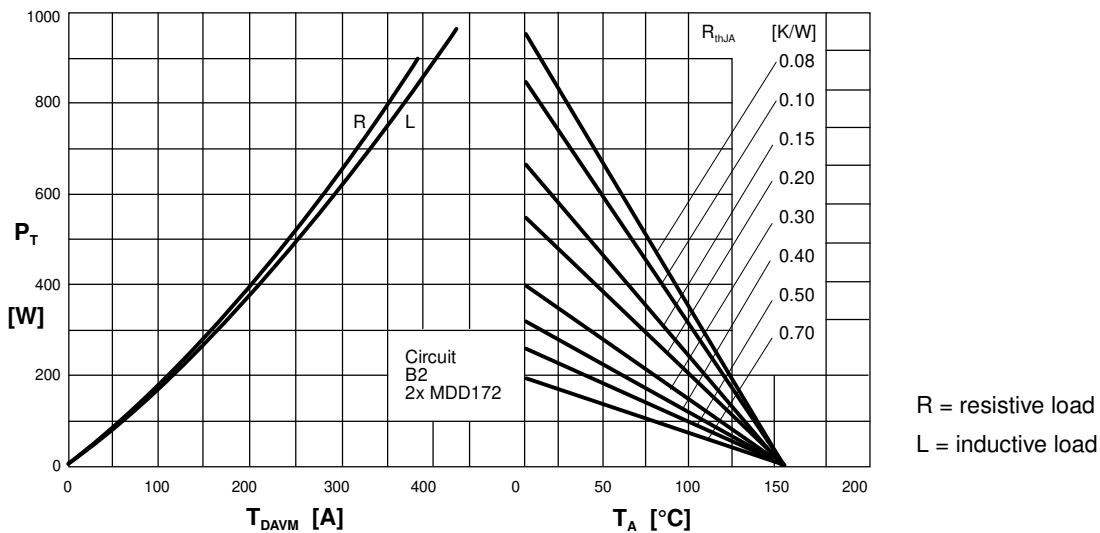


Fig. 4 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient



**Rectifier**



Fig. 5 Three phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature

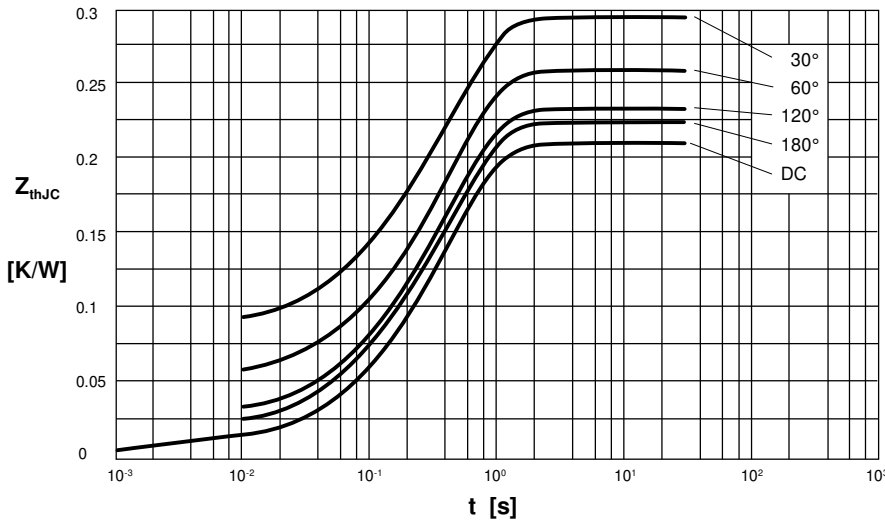


Fig. 6 Transient thermal impedance junction to case (per diode)

$R_{thJC}$  for various conduction angles  $d$ :

$d$	$R_{thJC}$ [K/W]
DC	0.210
180°	0.223
120°	0.233
60°	0.260
30°	0.295

Constants for  $Z_{thJC}$  calculation:

$i$	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0087	0.001
2	0.0163	0.065
3	0.1850	0.400



Fig. 7 Transient thermal impedance junction to heatsink (per diode)

$R_{thJK}$  for various conduction angles  $d$ :

$d$	$R_{thJK}$ [K/W]
DC	0.310
180°	0.323
120°	0.333
60°	0.360
30°	0.395

Constants for  $Z_{thJK}$  calculation:

$i$	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0087	0.001
2	0.0163	0.065
3	0.1850	0.400
4	0.1000	1.290